

Use Snubber Circuits to Dampen Noise in DC-DC Converters

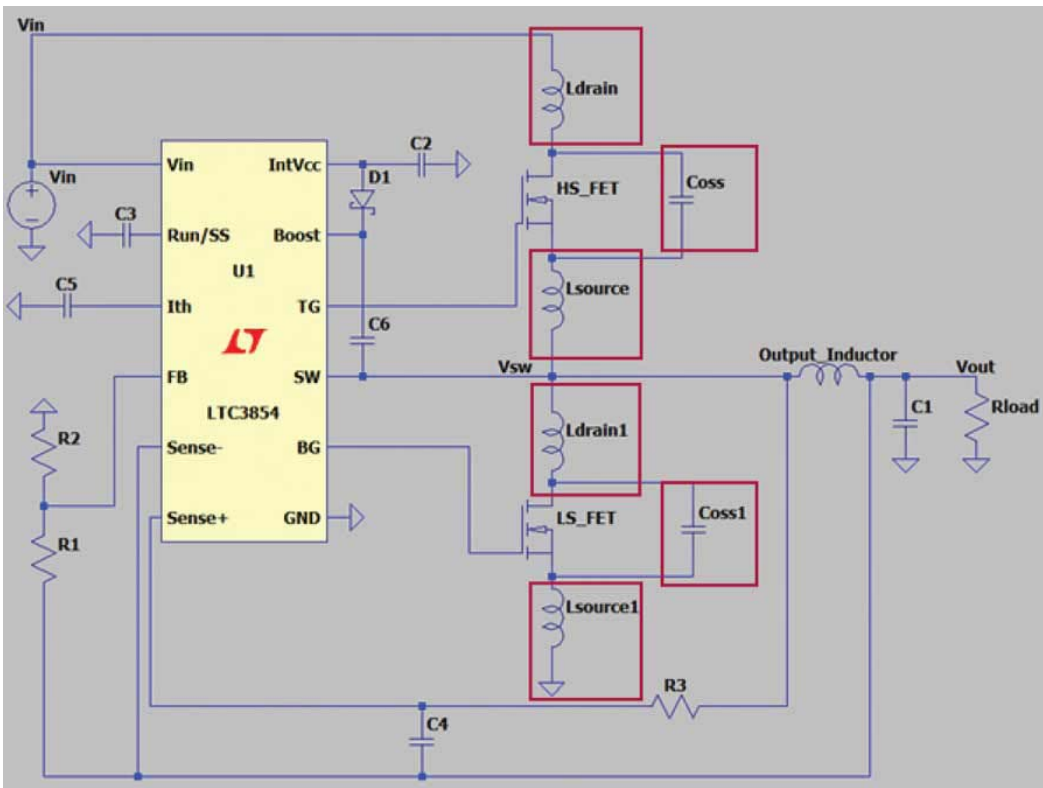
Switching noise in power converters can be difficult to eliminate. However, a well-designed and optimized snubber circuit helps dampen this ringing and improve overall efficiency.

Power designers are constantly pursuing [DC-DC converter designs](#) with higher efficiency and smaller sizes. These gains are often achieved by using faster switching frequencies to shrink [inductors](#) and capacitors in the solution.

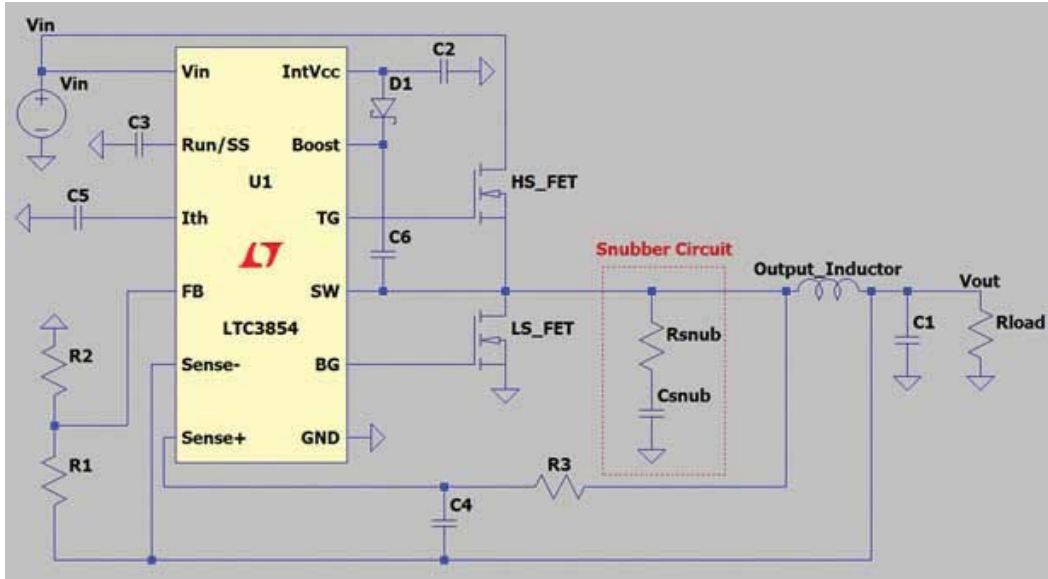
However, that also increases the impact of parasitics, which are unintended inductances and capacitances ema-

nating from PCB traces and power FETs themselves. At fast switching speeds, interaction with these parasitics can cause significant voltage overshoot and [ringing](#) at the switching (SW) node.

This ringing not only places additional voltage stress on the FETs, but it also causes unwanted [electromagnetic interference \(EMI\)](#). EMI disrupts the performance of a system



1. A typical buck converter with the circuit parasitics highlighted in red. Analog Devices



2. The position of a snubber circuit in a typical power-supply design. Analog Devices

through electromagnetic induction, electrostatic coupling, or conduction. It's a critical design challenge in industries like automotive, medical, and test and measurement, where meeting [strict EMI standards](#) is crucial for product certification and time-to-market.

Reducing ringing and other noise is often left until late in the design cycle, making it difficult to resolve. Using low-noise [DC-DC regulators](#) or fine-tuning the placement of power electronics on the PCB can help with that. But another approach — [the snubber circuit](#) — can effectively mitigate noise if those initial steps weren't taken.

Taking a synchronous buck regulator as an example, this article introduces the problems associated with switching ringing before explaining how to design and optimize a snubber to dampen it. Using [LTspice](#) and typical parasitic models, we will simulate the ringing seen on a standard PCB and demonstrate the impact of the calculated snubber values on both the ringing and the overall efficiency.

Where, When, and Why: Understanding Parasitics

In a buck converter, voltage overshoot and ringing at the switching node are a direct result of high speeds. These fast-switching frequencies interact with the parasitic inductances and capacitances in the circuit. Such parasitics are formed by copper traces in the PCB and the components themselves, particularly the [power FETs](#).

Essentially, the stray inductance from the PCB traces and the FET package forms an LC tank circuit with the FET's parasitic output capacitance (C_{OSS}). This makes both [PCB layout](#) and the selection of the MOSFET critical factors in [power-converter designs](#).

The magnitude of stray inductance varies from one design to another. But for the purposes of the simulations below, a

value of 5 nH around the FETs is a reasonable starting point. This value can be significantly higher with a poor layout, as inductance values can reach up to 10 nH for every 25 mm of trace length. *Figure 1* highlights a typical power-controller circuit using the [LTC3854](#), with the expected parasitics shown in red.

What's a Snubber Circuit and How Does It Work?

After identifying the switching noise and the parasitic elements that contribute to it, the next step is damping it. A snubber circuit — typically a series resistor-capacitor (RC) network — is commonly used to absorb the voltage spikes and ringing that appear at the SW node.

A snubber works by providing a controlled outlet for high-frequency energy from the parasitic LC tank. When the switch turns off, the snubber capacitor begins to charge, absorbing energy that would otherwise cause ringing. The snubber resistor then dissipates this stored energy as heat, effectively damping the oscillations.

By introducing a new resonant frequency and adding resistance to the circuit, the snubber reduces the peak voltage and duration of the ringing, protecting the power switches from overvoltage stress.

Figure 2 shows a typical buck converter with the snubber circuit positioned from SW node to ground (GND) as close as possible to the MOSFET.

The Snubbing Power of a Snubber Circuit

One of the keys to designing a snubber is determining the optimal resistance and capacitance values for the RC network used to damp voltage ringing and reduce EMI in switching circuits. The process involves finding the parasitic inductance and capacitance of the switching circuit

(through simulations or using an oscilloscope for actual hardware) to measure ring frequency and then calculating the snubber's characteristics from there. Here are the most important steps:

1. First, measure the ringing frequency of the switching node. This will be the peak of the first spike to the peak of the second spike. As a reminder, when measuring the parasitics on physical hardware with an oscilloscope, bandwidth limiting must be turned off. Also, a short scope ground must be used to ensure the ringing is visible.

2. Add a capacitance from SW to GND such that it reduces the ringing frequency (f_r) by approximately half the measured value above. Experiment with some different capacitance values here.

3. This will give the parasitic capacitance (C_p) by dividing that added capacitance by 3.

4. Knowing the parasitic capacitance, the parasitic inductance (L_p) can be calculated by:

$$L_p = \frac{1}{(2\pi f_r)^2 \times C_p} \quad (1)$$

The characteristic impedance is calculated by:

$$Z = \sqrt{\frac{L_p}{C_p}} \quad (2)$$

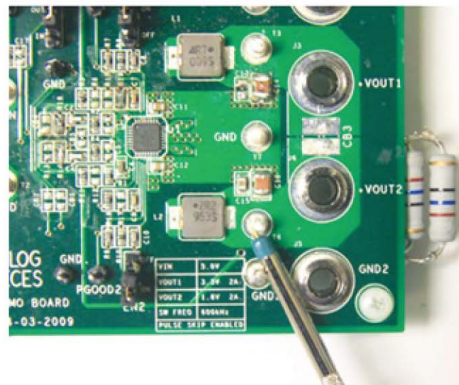
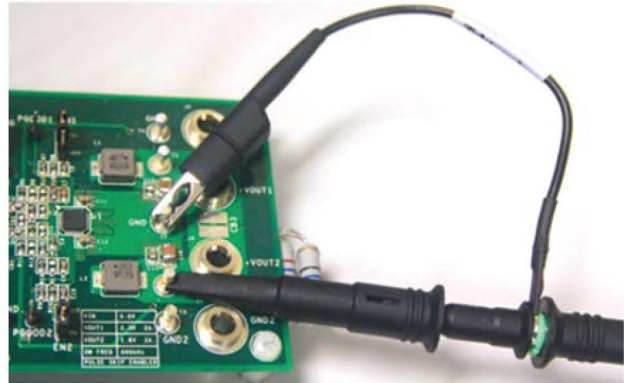
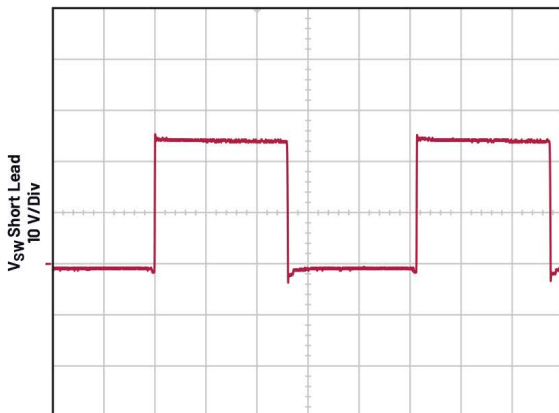
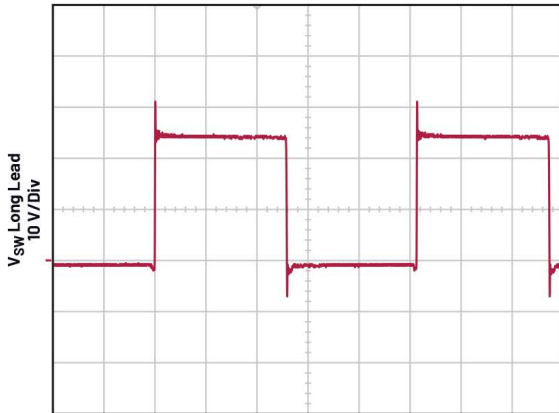
To attenuate the ringing, it will be necessary to use a snubber resistor that's approximately equal to the impedance calculated in *Equation 2*, generally a few ohms:

$$R(\text{SNUBBER}) \geq Z \quad (3)$$

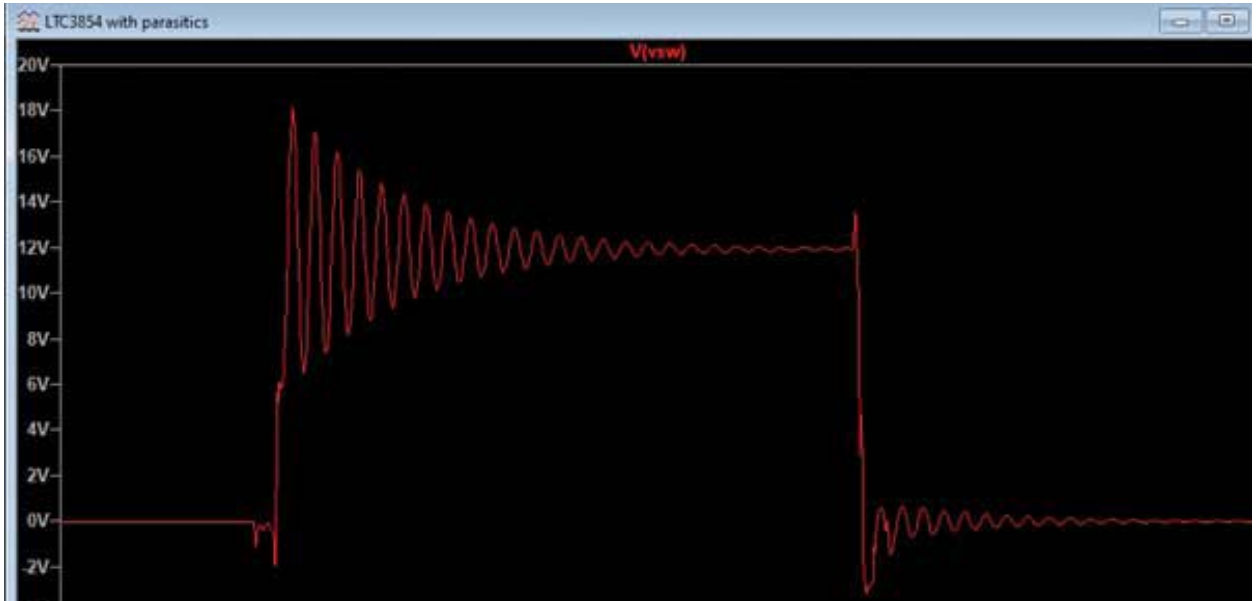
The capacitance value should then be selected by taking the C_p value calculated in *Equation 3* and increasing it by a factor of 1X to 4X higher.

Simulating and Analyzing a Snubber Circuit in LTspice

Having established the fundamentals of noise generation, measurement techniques, and initial snubber value calculations, the next step is to simulate these effects. This section uses LTspice to illustrate the impact of PCB parasitics on ringing and overshoot in the switching node, as well as the effectiveness of a snubber circuit in mitigating these effects. The following analysis will be conducted to compare



3. The difference between good and bad oscilloscope techniques. Analog Devices



5. Observing the switching node and associated overshoot and ringing. Analog Devices

Figure 5 illustrates the impact of these parasitics on the profile of the switching node. The LC tank formed by these elements causes significant overshoot and ringing.

As the simulation shows, the voltage peaks at just over 18 V, which is significantly higher than the expected 12 V. This overshoot is a major concern, as it can exceed the absolute maximum voltage ratings of the MOSFET, potentially damaging the component or reducing its long-term reliability. The ringing is also problematic, as it indicates the MOSFET isn't operating in its clearly defined on-off states.

The overall efficiency of the circuit is 96.3%, which seems high at first glance (Fig. 6). However, note that this efficiency is without a snubber. The following sections will show how adding a snubber, while crucial for mitigating ringing, will have a small, quantifiable impact on this efficiency.

Parasitic Model and Snubber Not Calculated

Figure 7 shows the same schematic as Figure 4, but with a simple RC snubber included from the switching node to ground. Note that this is a guessed starting snubber value and hasn't yet been calculated, so it will not be optimal.

--- Efficiency Report ---

Efficiency: 96.3%

Input: 25.5W @ 12V
Output: 24.6W @ 4.96V

Ref.	Irms	Ipeak	Dissipation
C1	391mA	828mA	1mW
C2	115mA	1416mA	0mW
C3	0mA	0mA	0mW
C4	1mA	1mA	0mW
C5	0mA	0mA	0mW
C6	159mA	1433mA	0mW
Coss	313mA	11138mA	0mW
Coss1	486mA	2823mA	0mW
Csnub	0mA	0mA	0mW
D1	82mA	1432mA	6mW
L1	5152mA	5790mA	154mW
Ldrain	3618mA	8473mA	13mW
Ldrain1	3782mA	6373mA	14mW
Lsource	3635mA	9063mA	13mW
Lsource1	3790mA	6427mA	14mW
Q1	3621mA	11247mA	295mW
Q2	3726mA	6623mA	173mW
R1	0mA	0mA	411µW
R2	0mA	0mA	78µW
R3	1mA	1mA	4mW
Rsnub	0mA	0mA	0µW
U1	177mA	1856mA	244mW

6. The overall efficiency of the original buck-converter. Analog Devices

First, determine the parasitic LC components of the circuit. The initial simulation (without a snubber) showed a ringing frequency of 23.41 MHz. Then, add a known capacitor from the SW node to ground to observe the change in the ringing frequency. A new simulation with a 14,000-pF capacitor at the SW node reduces the ringing frequency to 12 MHz.

Using the resonant frequency formula $f_0 = 1/(2 \times \pi \sqrt{LC})$ can determine the parasitic capacitance. The change in frequency is caused by the increase in total capacitance. The new total capacitance (C_{total}) is:

$$C_{total} = C_{parasitic} + C_{added}$$

The relationship between the original frequency (f_{old}) and the new frequency (f_{new}) is:

$$\frac{f_{old}}{f_{new}} = \sqrt{\frac{C_{total}}{C_{parasitic}}} \quad (4)$$

Solving for $C_{parasitic}$:

$$\frac{23.41 \text{ MHz}}{12 \text{ MHz}} = \sqrt{\frac{C_{parasitic} + 14,000 \text{ pF}}{C_{parasitic}}} \quad (5)$$

$$1.952 = \frac{C_{parasitic} + 14,000 \text{ pF}}{C_{parasitic}}$$

$$3.8 = \frac{C_{parasitic} + 14,000 \text{ pF}}{C_{parasitic}}$$

$$3.8 \times C_{parasitic} = C_{parasitic} + 14,000 \text{ pF}$$

$$2.8 \times C_{parasitic} = 14,000 \text{ pF}$$

$$C_{parasitic} = \frac{14,000 \text{ pF}}{2.8} = 5,000 \text{ pF}$$

This indicates that the circuit has a parasitic capacitance of approximately 5,000 pF. With the parasitic capacitance, the parasitic inductance can be calculated:

$$L_p = \frac{1}{(2 \pi f)^2 \times C_p} \quad (6)$$

$$L_p = \frac{1}{(\pi \times 23.41 \text{ MHz})^2 \times 5,000 \text{ pF}}$$

$$L_p = 9.2 \text{ nH}$$

The impedance of the circuit is calculated by:

$$Z = \sqrt{\frac{L_p}{C_p}} \quad (7)$$

$$Z = \sqrt{\frac{9.2 \text{ nH}}{5,000 \text{ pF}}}$$

$$Z = 1.35$$

— Efficiency Report —

Efficiency: 58.9%

Input: 41.8W @ 12V
Output: 24.6W @ 4.96V

Ref.	I _{rms}	I _{peak}	Dissipation
C1	405mA	828mA	1mW
C2	94mA	1405mA	0mW
C3	0mA	0mA	0mW
C4	1mA	1mA	0mW
C5	0mA	0mA	0mW
C6	56mA	552mA	0mW
Coss	238mA	7762mA	0mW
Coss1	163mA	1774mA	0mW
Csnub	2821mA	5795mA	0mW
D1	34mA	518mA	2mW
L1	5174mA	5790mA	155mW
Ldrain	5913mA	10678mA	35mW
Ldrain1	2094mA	3654mA	4mW
Lsource	5916mA	11194mA	35mW
Lsource1	2112mA	4524mA	4mW
Q1	5916mA	10919mA	788mW
Q2	2081mA	3638mA	70mW
R1	0mA	0mA	411µW
R2	0mA	0mA	78µW
R3	1mA	1mA	4mW
Rsnub	2821mA	5795mA	15920mW
U1	136mA	1512mA	161mW

9. The overall efficiency with initial snubber circuit values.

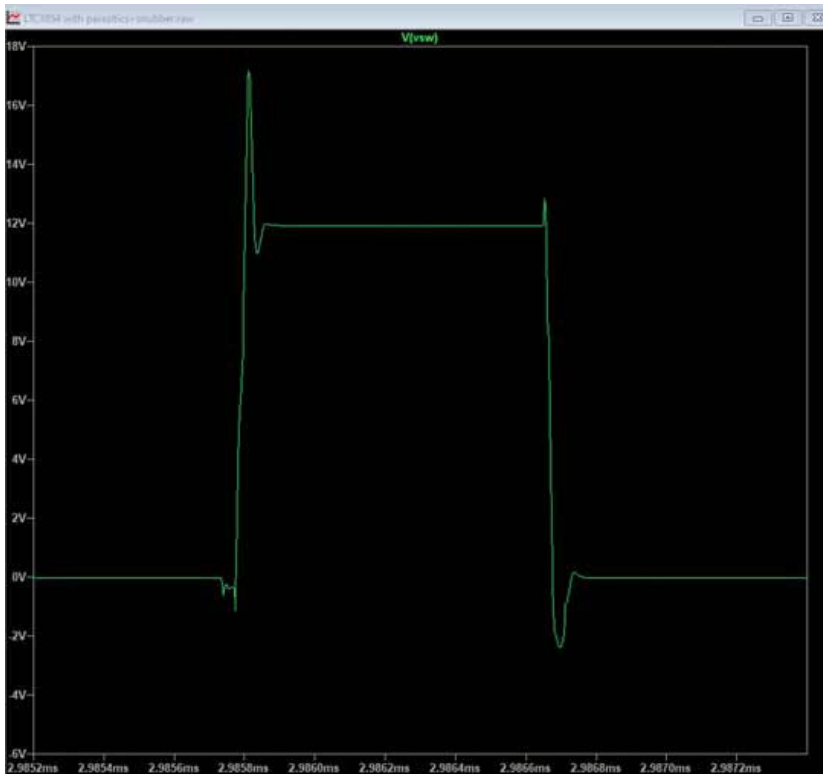
Analog Devices

The snubber resistance is set to be greater than the characteristic impedance noted above; in this case, a standard value of 1.5 Ω.

Next, the snubber capacitance, $C_{snubber}$, is typically sized to be at least equal to the parasitic capacitance, up to 4X this value. For the initial simulation, use a value that's double the parasitic capacitance to ensure sufficient energy absorption, setting $C_{snubber} = 2 \times C_{parasitic} = 2 \times 5,000 \text{ pF} = 10,000 \text{ pF}$. With the optimized snubber resistance and capacitance, plug these values back into the LTspice simulation to see how the circuit performs.

Figure 10 shows the resulting waveform with a 1.5 Ω + 10,000 pF snubber network. The ringing has been significantly dampened, as intended by the optimized design. The overshoot has also been reduced from more than 18 V to 17.2 V with these calculated snubber values. While some overshoot remains, the result highlights the inherent trade-off in snubber design: Perfectly eliminating all overshoot and ringing often requires snubber values that result in greater power loss and reduced efficiency.

Furthermore, the overall efficiency is now 94.8%, which is a significant improvement over the 58.9% seen with the uncalculated snubber (Fig. 11). There will always be some



10. SW node ringing using 1.5 Ω + 10,000 pF snubber circuit values. Analog Devices

--- Efficiency Report ---

Efficiency: 94.8%

Input: 25.9W @ 12V
Output: 24.6W @ 4.96V

Ref.	Irms	Ipeak	Dissipation
C1	373mA	834mA	1mW
C2	103mA	1197mA	0mW
C3	0mA	0mA	0mW
C4	1mA	1mA	0mW
C5	0mA	0mA	0mW
C6	100mA	1256mA	0mW
Coss	269mA	10639mA	0mW
Coss1	202mA	2516mA	0mW
Csnub	617mA	5148mA	0mW
D1	69mA	1142mA	5mW
L1	5069mA	5796mA	149mW
Ldrain	3477mA	11837mA	12mW
Ldrain1	3761mA	6226mA	14mW
Lsource	3485mA	12364mA	12mW
Lsource1	3762mA	5980mA	14mW
Q1	3481mA	11855mA	255mW
Q2	3751mA	6226mA	129mW
R1	0mA	0mA	410μW
R2	0mA	0mA	78μW
R3	1mA	1mA	4mW
Rsnub	617mA	5148mA	571mW
U1	0mA	0mA	175mW

11. Circuit efficiency with calculated 1.5 Ω + 10,000 pF snubber circuit values. Analog Devices

efficiency impact with a snubber, as the resistor dissipates a small amount of power. However, by optimizing the component values based on the parasitic LC tank, the impact on efficiency can be minimized.

Tackling the Complexities of Snubber Circuits

Understanding and mitigating switching node ringing is a critical step in designing a reliable switching regulator. As shown, this high frequency noise isn't an inherent flaw, but a direct consequence of the parasitic LC tank formed by PCB trace inductance and the switching components' capacitance.

By taking a methodical approach — accurately simulating the undamped ringing frequency and associated voltage overshoot — the problem can be demystified. This allows for calculating a precise snubber network value, where the resistor critically damps the circuit by matching the parasitic impedance, and the capacitor acts as an energy sink.

The simulation examples clearly demonstrate that a well-designed snubber is an elegant and effective solution. It trades a small, manageable power loss for a significant improvement in both EMI performance and system reliability. Ultimately, incorporating this simple but powerful RC network can quickly transform a noisy and potentially vulnerable power supply into a clean and dependable one, ensuring the longevity and compliance of the final product.

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Reference

Ballar, Wesley and Jacob Ciolfi. “[Lab Skills for Switch-Mode Power Supply Evaluation—Part 1: Measuring Voltage Ripple and Switching Node.](#)” *Analog Dialogue*, Vol. 59, January 2025.